

**Key Parameters**

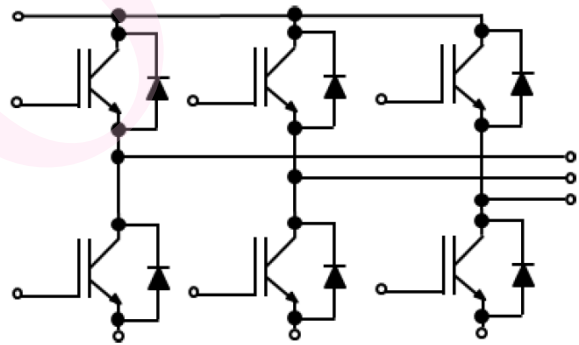
V_{CES} = 650V
 I_c = 20A

Features

- Low $V_{ce(sat)}$
- Fast switching
- High ruggedness
- High short circuit capability

Applications

- Inverter for motor drive
- Water pumps
- Wind turbines



Equivalent Circuit Schematic

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Absolute Maximum Ratings: IGBT, Inverter						
Symbol	Characteristic	Value	Unit			
V_{CES}	Collector-Emitter Voltage	650	V			
I_{CDC}	Continuous DC Collector Current	20	A			
I_{CRM}	Peak Collector Current	40	A			
V_{GES}	Gate-Emitter Voltage	± 20	V			
$P_{D(max)}$	Total Power Dissipation ($T_c=25^\circ\text{C}$, $T_j=175^\circ\text{C}$)	70	W			
IGBT Characteristics						
Symbol	Characteristic	Conditions	Value			Unit
			Min.	Typ.	Max.	
BV_{CES}	Collector-Emitter breakdown Voltage	$V_{GE}=0V, I_C=250\mu A, T_{vj}=25^\circ\text{C}$	650			V
I_{CES}	Collector-Emitter leakage Current	$V_{CE}=650V, V_{GE}=0V, T_{vj}=25^\circ\text{C}$			1.0	mA
I_{GES}	Gate-Emitter leakage Current	$V_{CE}=0V, V_{GE}=\pm 20V, T_{vj}=25^\circ\text{C}$			400	ηA
$V_{GE(th)}$	Gate-emitter Threshold Voltage	$V_{GE}=V_{CE}, I_C=250\mu A, T_{vj}=25^\circ\text{C}$	5.0	6.0	7.0	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=20A, V_{GE}=15V, T_{vj}=25^\circ\text{C}$		1.70	2.00	V
		$I_C=20A, V_{GE}=15V, T_{vj}=150^\circ\text{C}$		2.15		V
Q_G	Gate Charge	$V_{CC}=300V, V_{GE}=0/15V, I_C=20A, T_{vj}=25^\circ\text{C}$		45		ηC
C_{iss}	Input Capacitance	$V_{CE}=25V, V_{GE}=0V, f=1\text{MHz}, T_{vj}=25^\circ\text{C}$		0.93		ηF
C_{oss}	Output Capacitance			0.085		ηF
C_{rss}	Reverse Transfer Capacitance			0.016		ηF
$t_{d(on)}$	Turn-on Delay Time	$I_C=20A, V_{CE}=300V, V_{GE}=\pm 15V, R_G=22\Omega, T_{vj}=25^\circ\text{C}, L_{load}=0.82\text{mH}$ Energy loss include tail and diode reverse recovery		29		ηs
t_r	Rise Time			44		ηs
$t_{d(off)}$	Turn-off Delay Time			77		ηs
t_f	Fall Time			94		ηs
E_{on}	Energy Dissipation During Turn-on Time			0.4		mJ
E_{off}	Energy Dissipation During Turn-off Time			0.28		mJ
$t_{d(on)}$	Turn-on Delay Time	$I_C=20A, V_{CE}=300V, V_{GE}=\pm 15V, R_G=22\Omega, T_{vj}=150^\circ\text{C}, L_{load}=0.82\text{mH}$ Energy loss include tail and diode reverse recovery		30		ηs
t_r	Rise Time			46		ηs
$t_{d(off)}$	Turn-off Delay Time			97		ηs
t_f	Fall Time			135		ηs
E_{on}	Energy Dissipation During Turn-on Time			0.6		mJ
E_{off}	Energy Dissipation During Turn-off Time			0.38		mJ
$I_{C(SC)}$	SC Data	$t_{sc}\leq 5\mu s, V_{GE}=15V, T_{vj}=25^\circ\text{C}, V_{CC}\leq 400V,$		60		A

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Absolute Maximum Ratings: Diode, Inverter						
Symbol	Characteristic	Value	Unit			
V_{RRM}	Repetitive peak reverse voltage	650	V			
I_F	Continuous DC forward current	20	A			
I_{FRM}	Repetitive peak forward current	40	A			
Diode Characteristics						
Symbol	Characteristic	Conditions	Value			Unit
			Min.	Typ.	Max.	
V_F	Forward Voltage	$I_F=20A, T_{vj}=25^{\circ}C$		1.4	1.7	V
		$I_F=20A, T_{vj}=150^{\circ}C$		1.2		V
Q_{rr}	Recovered Charge	$I_F=20 A$		0.33		μC
I_{rrm}	Peak Reverse Recovery Current	$V_R=300V$		8.4		A
E_{rr}	Reverse Recovery Energy	$-di_F/dt =367A/\mu s$ $T_{vj}=25^{\circ}C$		0.02		mJ
Module Characteristics						
Symbol	Characteristic	Conditions	Value			Unit
			Min.	Typ.	Max.	
V_{isol}	Isolation voltage	$t=1min, f=50Hz$	2500			V
T_{jmax}	Maximum Junction Temperature				175	$^{\circ}C$
T_{vjop}	Operating Junction Temperature		-40		150	$^{\circ}C$
T_{stg}	Storage Temperature		-40		125	$^{\circ}C$
$R_{CC'+EE'}$	Module lead resistance terminal to chip			9.5		m Ω
L_{SCE}	Stray Inductance, Module			25		nH
$R_{\theta jc}$	Junction-to Case	per IGBT-inverter		1.95		$^{\circ}C/W$
		per Diode-inverter		2.5		$^{\circ}C/W$
$R_{\theta cs}$	Case to Sink	per IGBT-inverter		0.81		$^{\circ}C/W$
		per Diode-inverter		1.0		$^{\circ}C/W$
M_t	Module force for module mounting		30		50	N
G	Weight of Module			10		g
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• Typical Electrical Characteristics

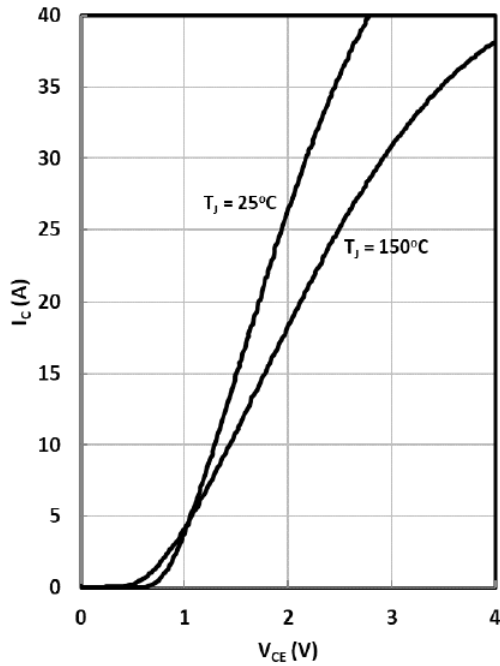


Fig. 1 IGBT (Inverter) Output Characteristics

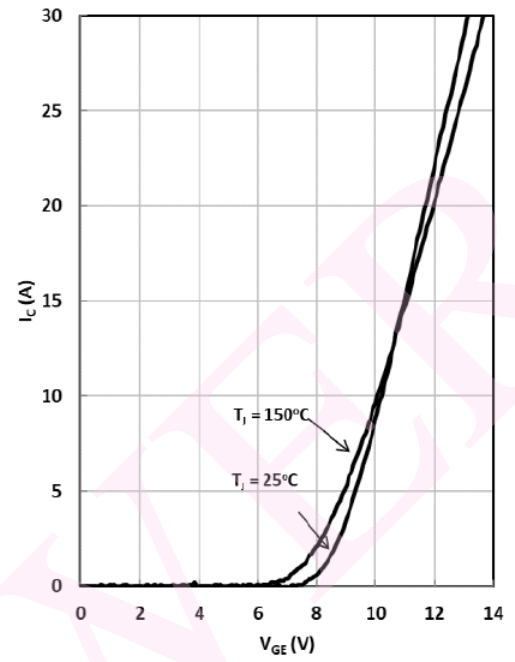


Fig. 2 IGBT (Inverter) Transfer Characteristics

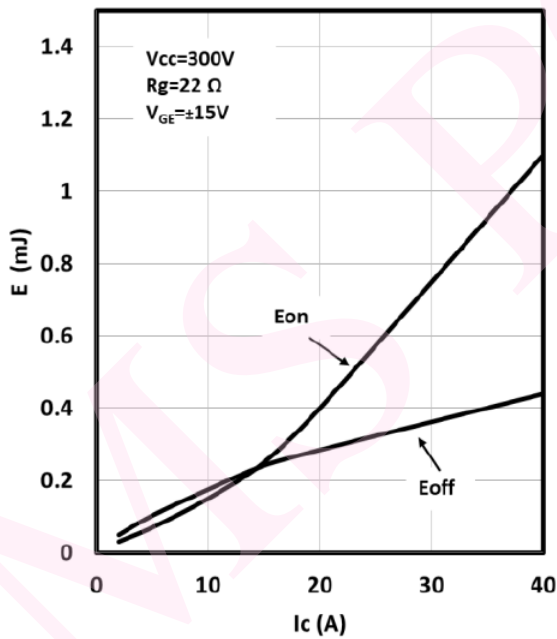


Fig. 3 IGBT (Inverter) Switching Loss vs. Ic

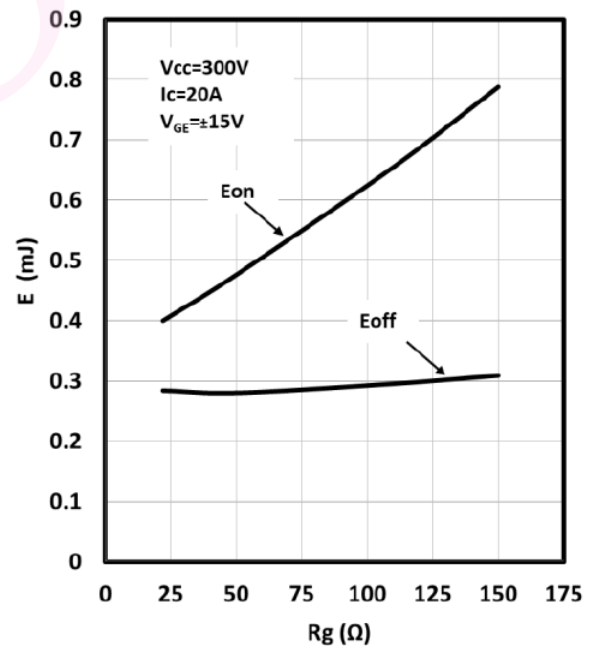


Fig. 4 IGBT (Inverter) Switching Loss vs. Rg

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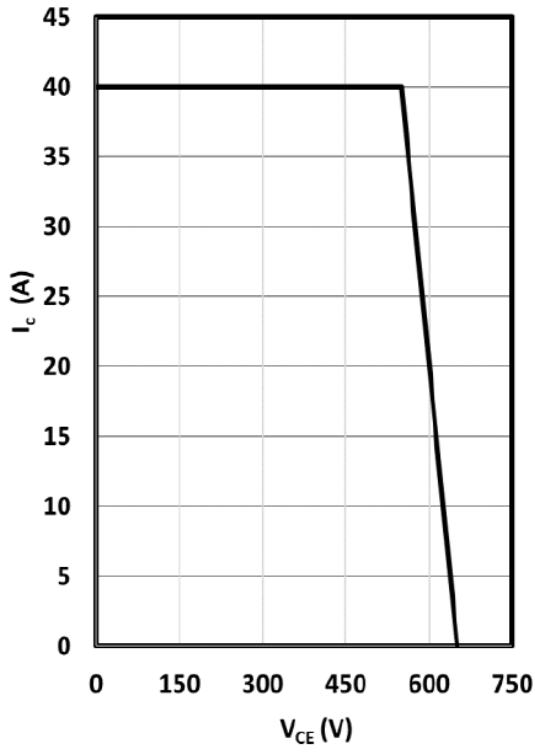


Fig. 5 RBSOA

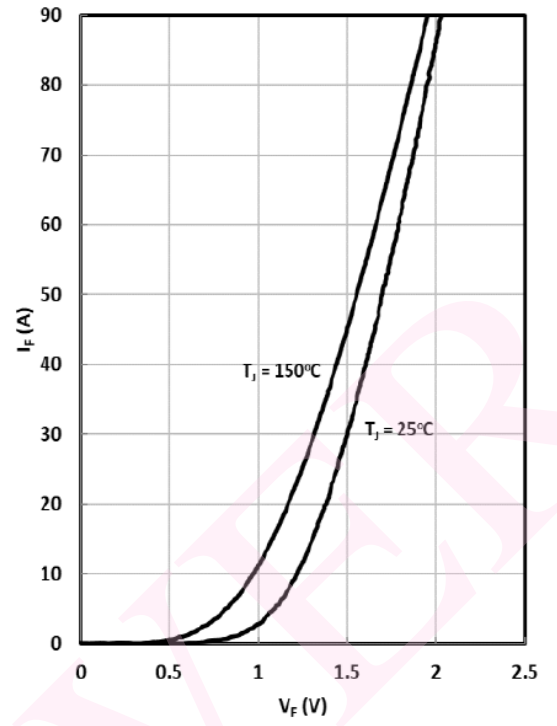
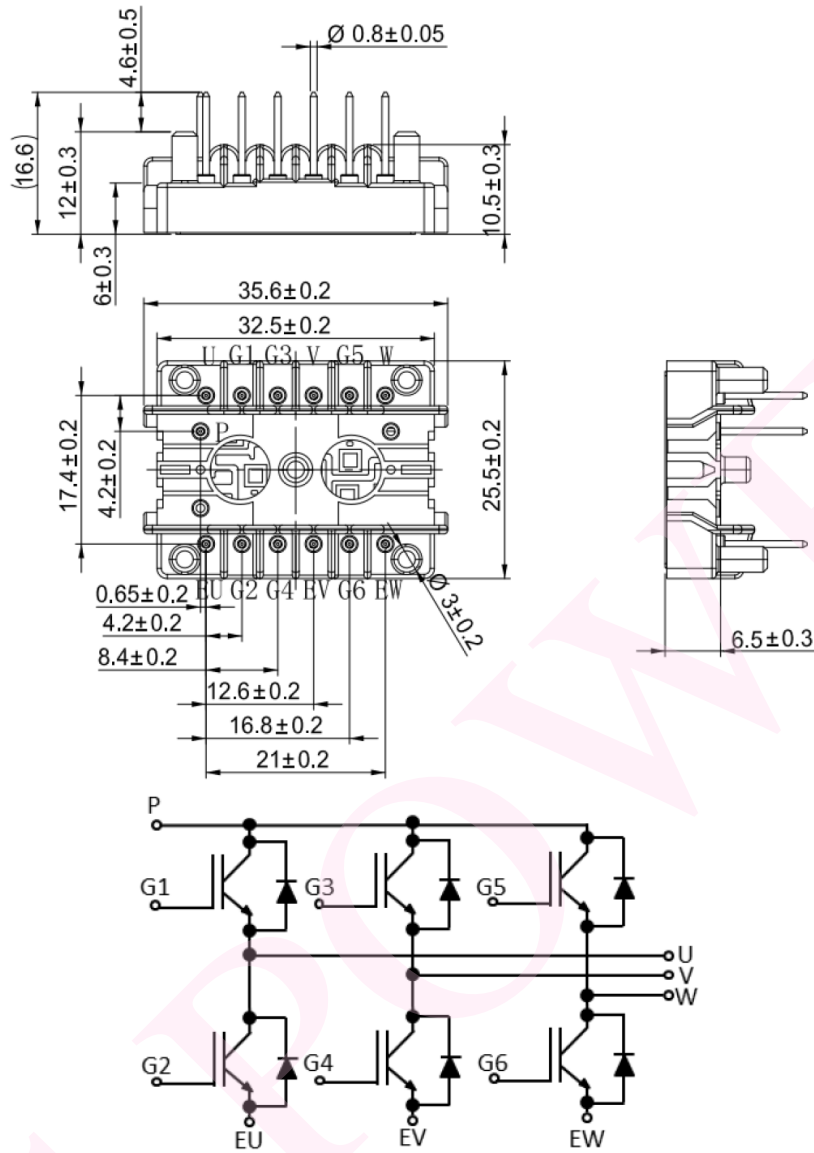


Fig. 6 Diode (Inverter) Forward Characteristics

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